

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, OPTICAL MEMBER FOR USE IN CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, MANUFACTURING METHOD OF THIN FILM TRANSISTOR, AND MANUFACTURING METHOD OF MATRIX CIRCUIT SUBSTRATE OF DISPLAY

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

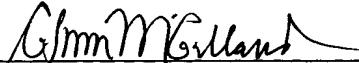
- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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DISPLAY

STATEMENT OF RELEVANCY

Reference AV and AW of Form PTO-1449:

This documents are disclosed in the body of the specification.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 239499US2		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Yukio TANIGUCHI, et al.			
		FILING DATE Herewith		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA							
AB							
AC							
AD							
AE							
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
AO							
AP							
AQ							
AR							
AS							
AT							
AU							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AV	Masakiyo MATSUMURA, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", Surface Science, Vol. 21, No. 5, pp. 278-287, 2000.					
	AW	2000-306859, published November 2, 2000.					
	AX	M. NAKATA, et al., "TWO-DIMENSIONALLY POSITION-CONTROLLED ULTRA-LARGE GRAIN GROWTH BASED ON PHASE-MODULATED EXCIMER-LASER ANNEALING METHOD", Department of Physical Electronics, Tokyo Institute of Technology, Electrochemical Society Proceedings, Vol. 2000-31, pgs. 148 – 154.					
	AY	Wen-Chang YEH, et al., "EFFECTS OF A LOW-MELTING-POINT UNDERLAYER ON EXCIMER-LASER-INDUCED LATERAL CRYSTALLIZATION OF Si THIN-FILMS", Jpn. J. Appl. Phys. Vol. 40 (2001), Part 1, No. 5A, May 2001, pp. 3096 - 3100					
	AZ	Y. SANO, et al., "HIGHLY PACKED AND ULTRA-LARGE Si GRAINS GROWN BY A SINGLE-SHOT IRRADIATION OF EXCIMER-LASER LIGHT PULSE", Department of Physical Electronics, Tokyo Institute of Technology, (8 pages)				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
<small>*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							